Supply Voltage	0.4V to 7V
Operating Temperature Range	40°C to +85°C
Junction Temperature	125°C
Storage Temperature Range	65°C to +150°C

#### ELECTRICAL CHARACTERISTICS

 $V_{IN}$  = 2.5V,  $V_{CTRL}$  = 3.3V,  $V_{REF}$  = 0.5 $V_{IN}$ ,  $C_{OUT}$  = 10 $\mu$ F (Ceramic),  $T_A$  = 25°C, unless otherwise specified. (Note 1)

Parameter	rameter Symbol Test Conditions							
Input Voltage Range (DDR 1/2) (Note 5)	V <sub>IN</sub>	Keep V <sub>CTRL</sub> V IN on operation power on and power off sequences	1.6	2.5/1.8	-	v		
	V <sub>CNTL</sub>	I <sub>OUT</sub> = 0mA	3.0	3.3	6			
Output Voltage	V <sub>OUT</sub>	louτ = 0mA		Vref		V		
Output Offset Voltage	Vos	No Load	-20	-	20	mV		
Load Regulation	V <sub>lor</sub>	louτ = 0.1mA to +2A	-	10	25	mV		
(DDR 1/2)	LOR	Ιουτ = 0.1mA to -2A	-	10	25			
Quiescent Current	۱ <sub>۵</sub>	$V_{REF} < 0.2V, V_{OUT} = OFF$	-	8	30	μA		
Operating Current of $V_{CNTL}$	ICNTL	No Load	-	3	10	mA		
Bias Current of VREF		V <sub>REF</sub> = 1.25V	-	-	1	μA		
Current Limit	lı.	Note 4	2.2	3	4.5	А		
Thermal Protection								
Thermal Shutdown Temperature (Note 5)	T <sub>SD</sub>	3.3V V CNTL 5V Guaranteed by design	125	150	-	°C		
Thermal Shutdown Hysteresis		Guaranteed by design	-	30	-	°C		
Shutdown Specifications								
Shutdown Threshold	Vtrigger	Output ON ( V <sub>REF</sub> = ZeroV>1 .25V)	0.8	-	-	V		
Shutdown Threshold	Vtrigger	Output OFF ( V <sub>REF</sub> = 1.25V> ZeroV)	-	-	0.2	v		
Thermal Resistance	θја			160		°C/W		
	өлс			40		0, •••		

Note 1 . Specifications are tested for production at  $T_A = 25^{\circ}C$ . Specifications over the -40°C to 85°C operating temperature range are assured by design, characterization and correlation with Statistical Quality Controls (SQC). Note 2.  $V_{os}$  offset is the voltage measurement defined as  $V_{out}$  subtracted from  $V_{REF}$ .

Note 3. Load regulation is measured at constant junction temperature, using pulse testing with a low ON time.

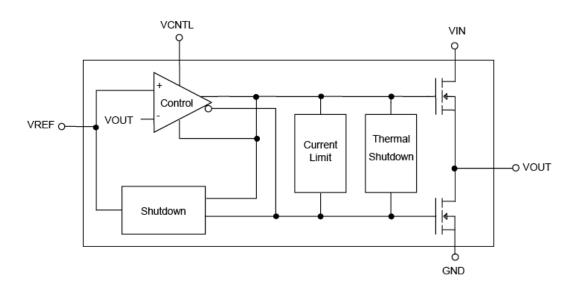
Note 4. Current limit is measured by pulsing a short time.

Note 5. In order to safely operate your system, V\_{\_{\rm CTRL}} must be >  $\rm \,V_{_{\rm IN}}$ 

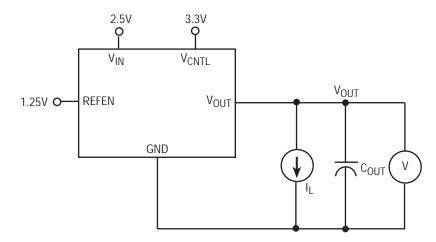
#### **PIN DESCRIPTIONS**

Pin Name	Pin Number	Description (8 pin NSOIC)
Vin	1	Power Input Voltage
GND	2	Ground
REFEN	3	Reference Voltage Input
V <sub>OUT</sub>	4	Output Voltage
V <sub>cntl</sub>	5	Voltage for the driver circuit and all analog blocks
V <sub>CNTL</sub>	6	Voltage for the driver circuit and all analog blocks
V <sub>CNTL</sub>	7	Voltage for the driver circuit and all analog blocks
V <sub>CNTL</sub>	8	Voltage for the driver circuit and all analog blocks

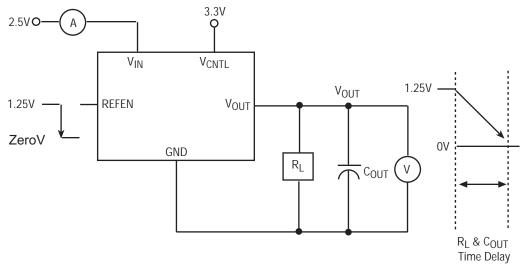
**BLOCK DIAGRAM** 



3

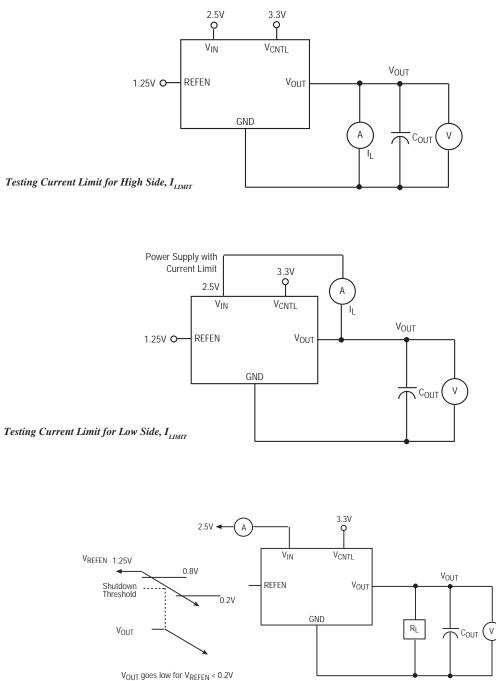


Testing Output Voltage Tolerance,  $\Delta V_{LOAD}$ 



```
Testing Current in Shutdown Mode, I<sub>SHDN</sub>
```

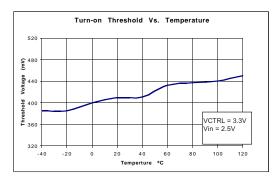
#### **TEST CIRCUITS**

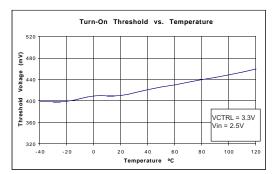


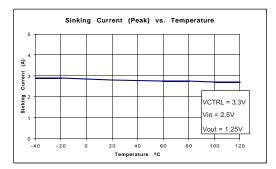
Testing REFEN Pin Shutdown Threshold, ,  $V_{TRIGGER}$ 

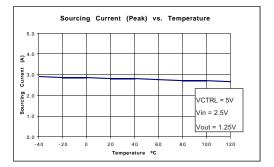
V<sub>OUT</sub> goes low for V<sub>REFEN</sub> > 0.8V

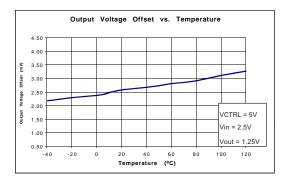
#### **TYPICAL PERFORMANCE CHARACTERISTICS**

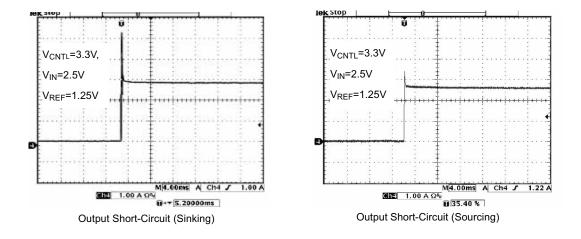


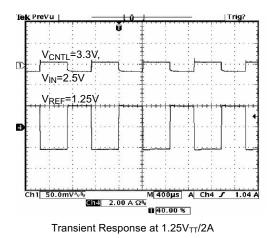


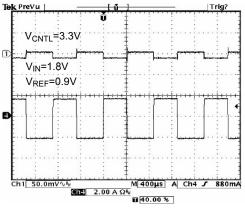












Transient Response at 0.9VTT/2A

#### Internal parasitic diode

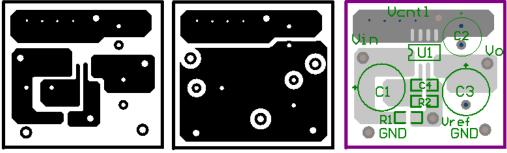
Avoid forward-biasing the internal parasitic diode,  $V_{OUT}$  to  $V_{CNTL}$ , and  $V_{OUT}$  to  $V_{IN}$ . Positive voltage should not be applied to the output if  $V_{IN}$  and  $V_{CNTL}$  are not present.

# Considerations for designing, resistance of voltage divider

When the reference voltage is programmed below 0.2V the pulldown capability of the internal NMOS transistor is limited. It is recommened to place a filter capacitor from  $V_{RE}$  to ground in order to reduce sensitivity to noise and improve power up characteristics (soft start).

#### Layout Considerations

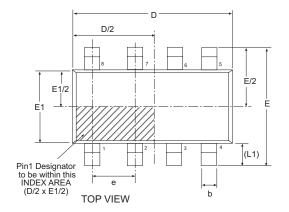
The SP2996B is offered in the NSOIC-8 package , resulting in attention needing to be paid to dissipating heat effectively when it operates in high current. In order to prevent maximum junction temperature from being exceeded, suitable copper area at NCNTL pins is available, and by taking advantage of this, much heat dissipation is attained. Use vias to direct heat into the bottom layer as the layout examples show below. All capacitors should be placed as close as possible to relative pins.

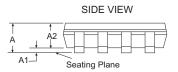


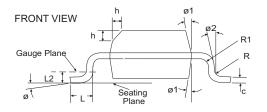
Top layer

Bottom layer

Placement







8 Pin NSOIC JEDEC MS-012 Variation AA											
SYMBOL		sions in Milli rolling Dime		Dimensions in Inches Conversion Factor: 1 Inch = 25.40 mm							
	MIN	NOM	MAX	MIN	NOM	MAX					
Α	1.35	-	1.75	0.053	-	0.069					
A1	0.10	-	0.25	0.004	-	0.010					
A2	1.25	-	1.65	0.049	-	0.065					
b	0.31	-	0.51	0.012	-	0.020					
с	0.17	-	0.25	0.007	-	0.010					
E		6.00 BSC		0.236 BSC							
E1		3.90 BSC			0.154 BSC						
е		1.27 BSC		0.050 BSC							
h	0.25		0.50	0.010	-	0.020					
L	0.40	-	1.27	0.016	-	0.050					
L1		1.04 REF		0.041 REF							
L2		0.25 BSC			0.010 BSC						
R	0.07	-	-	0.003	-	-					
R1	0.07	-	-	0.003	-	-					
ø	00	-	80	00	-	80					
ø1	5°	-	15°	50	-	15°					
ø2	00	-	-	00	-	-					
D		4.90 BSC		0.193 BSC							
SIPEX	SIPEX Pkg Signoff Date/Rev: JL Aug16-05 / Rev A										

#### PART NUMBER

#### **TEMPERATURE RANGE**

#### PACKAGE

Available in lead free packaging. To order add "-L" suffix to part number. Example: SP2996BEN/TR = standard; SP2996BEN-L/TR = lead free.

/TR = Tape and Reel Pack quantity is 2,500 for NSOIC.



# **Appendix and Web Link Information**

For further assistance:

Email: WWW Support page: Sipex Application Notes: Product Change Notices: Sipexsupport@sipex.com http://www.sipex.com/content.aspx?p=support http://www.sipex.com/applicationNotes.aspx http://www.sipex.com/content.aspx?p=pcn



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The following sections contain information which is more changeable in nature and is therefore generated as appendices.

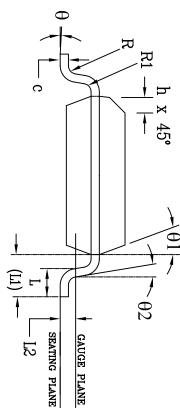
- 1) Package Outline Drawings
- 2) Ordering Information

If Available:

- 3) Frequently Asked Questions
- 4) Evaluation Board Manuals
- 5) Reliability Reports
- 6) Product Characterization Reports
- 7) Application Notes for this product
- 8) Design Solutions for this product

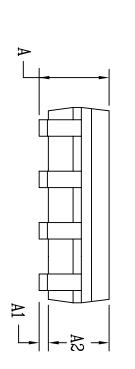
Front View

Side View

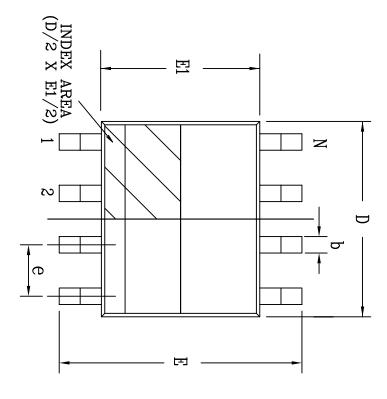


				GAUGE PLANE	θ2	zo	θ2	θ1	θ	<u>,</u> z	- 12		<b>–</b>	Ъ	ი <u>[</u>	- <u> </u>	י רי		- A2	A1	A	SYMBOLS	8 Pin				
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Top View



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**APPLICATION NOTE** 



# Introduction

Double Data Rate (DDR) SDRAM is finding its way into more and more consumer appliances, in addition to its traditional market of PCs and servers. This has led to lower cost requirements for DDR power management, in particular DDR termination. High end servers and PCs tend to use DC/DC buck converter solutions, due to higher current demands (>4A). However, these solutions are costly and over-specified for smaller systems where a lower number of memory devices are used. Initial theories suggested that even in such situations, a capability of up to 3A for termination would be required. However when the overall current requirements are considered, as opposed to just the instantaneous peaks, the solution becomes less onerous.

# Load Calculations

In DDR DRAM systems. Stub Series Terminated Logic (SSTL) is the preferred termination architecture for critical control and data signals. It dramatically reduces unwanted reflections and Electromagnetic Interference (EMI), thus improving speed and noise margins. The JEDEC SSTL 2 standard defines the termination scheme featured in Figure 1.

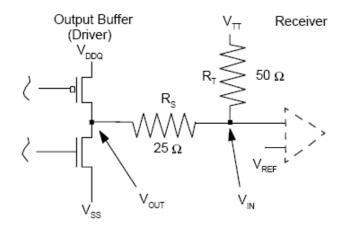


Figure 1 SSTL 2 Standard

In Figure 1, the value of  $R_T$  can be either 50 $\Omega$  (Class 1 Termination) or 25 $\Omega$  (Class 2 Termination). Since 25 $\Omega$  represents the greater load for the V<sub>TT</sub> supply, this value will be used for the remaining calculations.

The requirement is that V<sub>OUT</sub> has sufficient magnitude when driving into the termination network, to establish  $V_{IN}$  as greater than or equal to the minimum threshold at the receiver to guarantee correct recognition of a 1 or 0. From this requirement, using SSTL 2 data [1] we can derive the supply current  $(I_{TT})$  for  $V_{TT}$ :

 $V_{INmin} = 405 mV$ R<sub>T</sub> = 25Ω  $R_s = 25\Omega$ 

 $I_{TT} = (V_{TT} - V_{INmin}) \div R_T = 16.9 \text{mA}$ 

This represents the minimum current required, in practice the figure is closer to 20mA.

Consider the case for 1Gb 32 bit system. This is typically organised as 13 multiplexed address lines, 32 data lines, 12 strobe/mask and various command signals (RAS, CAS, WE, CKE, BA, etc). The total is around 64 depending upon exact implementation. With each terminated signal consuming ~20mA, this gives a total load of 1.28A max. This brings into consideration linear solutions, such as SP2996B, which as can be seen from Figure 2, offers a simpler, smaller and much more cost effective solution than any switching equivalent. Additional benefits over buck converters are improved speed, lower noise and vastly reduced possibility of EMI issues.

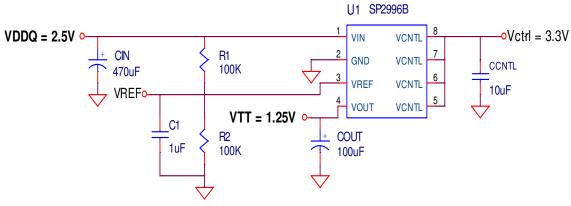


Figure 2 SP2996B Schematic

# **Averaging Considerations**

The above calculations represent a true worst case scenario, which in practice is unlikely to occur, and certainly cannot persist. This figure assumes that all the data, address and control lines are at the same state in a single instant. This is clearly not possible. Further, even if the data and address lines were all at 1, for example, this would only be a momentary incidence. Typically the data and address lines average out over a period of time to an RMS voltage much closer to Vtt (empirical research and measurements suggest the maximum peak load of 1.3A translates to an average load of around 250mA). In order to deliver peak currents, (DDR cycles last only in the order of tens of ns) an output capacitor of reasonable value could absorb the instantaneous changes and average them out to the lower, average current demand. This will then become the average current supplied by the SP2996B. For a DDR cycle that lasts 20ns (dependent on clock speed), even with a worst case 1.26A load, this results in <30nC of charge, which would deplete a 100uF cap by <500uV. Thus a number of repetitive cycles could be tolerated before the regulator must top up the capacitor.

# Power Calculations

The max VDD is 2.5V, with a regulation of 250mA down to the 1.25 volts required for VTT, the power dissipated is 313mW. This is easily within the capability of the SP2996B which has a  $\theta_{JA}$  of 128°C/W, giving a 40°C rise over ambient temperature.

## **DDR2 Specifications**

In order to facilitate lower power consumption and higher data rates, DDR2 operates from 1.8V supply with  $V_{TT} = 0.9V$ . The revised JEDEC SSTL 1.8 termination load is now as shown in Figure 3. With the lower value of  $V_{DDQ}$  (1.8V nominal) it is likely that the output transistors will now operate more in the linear region. Thus a specification for the ON resistance ( $R_{ON}$ ) is defined as <21R to ensure the required current delivery ( $I_{TT}$ )into the termination network. Using this value, along with Rs and RT gives the following:

This represents a minimum value, (ie  $R_{ON} = 21\Omega$ ), typically values are around 16mA.

Using the same 1Gb scenario as earlier, this gives a total peak load of  $64 \times 16\text{mA} = 1.02\text{A}$ . The same averaging effects apply with DDR2, hence a realistic average termination current would be 210mA. With a V<sub>DDQ</sub> now equal to 1.8V, the power handling required by the SP2996 goes down to 210mA  $\times$  0.9V = 192mW for the DDR2 termination. This would give a temperature rise over ambient of approximately 25 °C.

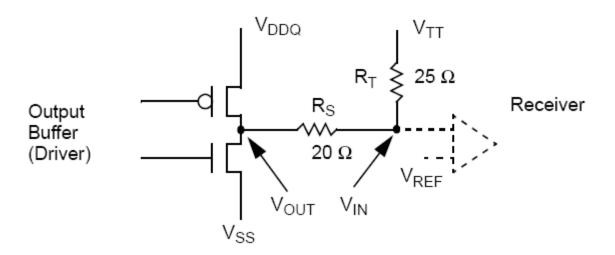


Figure 3 JEDEC SSTL 1.8 Load

# System Applications and the Vddq Supply

The demands for  $V_{DDQ}$  are somewhat higher than  $V_{TT}$ , usually necessitating the use of DC-DC buck solutions. For smaller systems, the load is in the range of 1-3A and can be considerably higher for larger capacity. Figure 4 shows a complete solution for  $V_{DDQ}$  and  $V_{TT}$  from a 3.3V to 5V supply for systems with a  $V_{DDQ}$  requirement of <4A. Figure 5 shows a complete solution derived from a 12V supply for systems with a  $V_{DDQ}$  in the 2A to 10A range. This system uses ceramic caps, and its synchronous nature allows it to efficiently develop lower output voltages, thereby making it well suited to DDR2 applications. The same solution can also be used with a 5V input by component value changes to the compensation network. (Contact Sipex applications support for full details.)

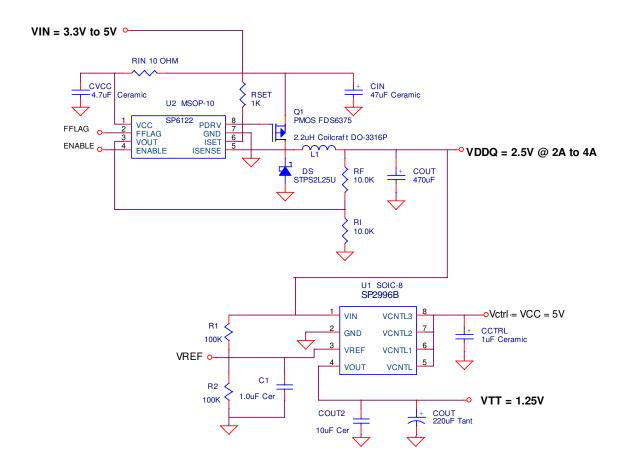


Figure 4 Complete DDR Solution 3.3V to 5V Input, VDDQ <4A

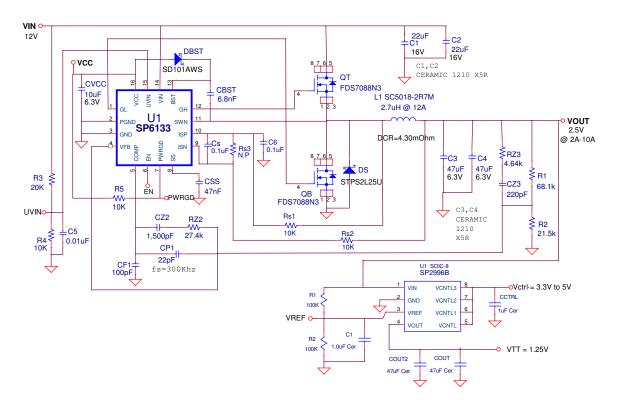


Figure 5 Complete DDR Solution 12V Input, VDDQ <10A

# **Conclusion**

For smaller DDR and DRR2 applications (e.g., Digital Set Top Boxes) the SP2996 offers large space (75%) and cost (60%) savings over DC-DC based implementations. Its simple architecture and high speed reduce component count, while offering fast transient response and zero switching noise. When used in conjunction with either of the  $V_{DDQ}$  solutions highlighted, a complete memory power management is realized.

### **References**

- [1] JESD8-9B Stub Series Terminated Logic for 2.5V
- [2] JESD8-15A Stub Series Terminated Logic for 1.8V



# **Design Solution 2**

# SP2996 DDR Termination Circuit Using Ceramic Capacitors

Date: January 2, 2006

**Designed by:** Mark Boermeester (mboermeester@sipex.com)

Part Number: SP2996B

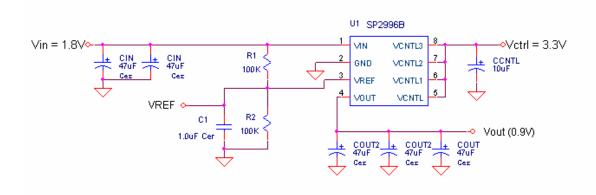
Application Description: Linear regulator for DDR memory termination

### **Electrical Requirements:**

Input Voltage	1.8V
Output Voltage	0.9V
Output Current	2A

## **Circuit Description:**

This Design Solution provides transient response measurement for the SP2996B DDR termination device using different values output capacitors. In order to demonstrate stable operation the circuit was tested with ceramic capacitors under transient loads.

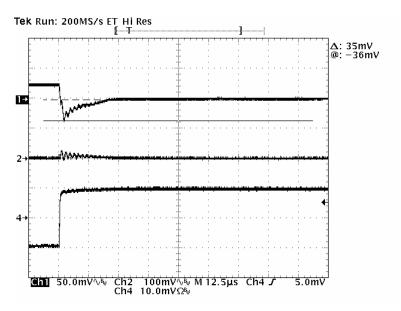




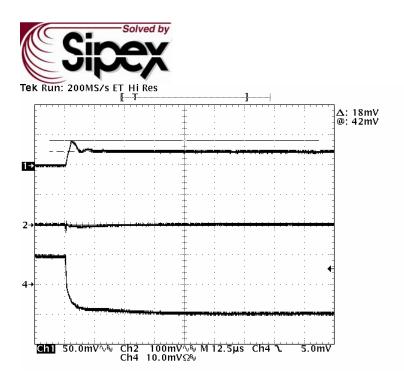
The following figures show scope plots for increase and decrease in load current. Output voltage is represented by channel 1, reference voltage by channel 2 and output current by channel 4 (2A/DIV).

Test 1

Output Capacitance: 3 x 47uF (141 uF total) Transient Description: Sink to Source Output Voltage Overshoot: 35mV

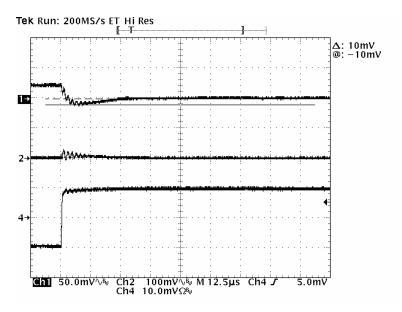


Transient Description: Source to Sink Output Voltage Overshoot: 18mV

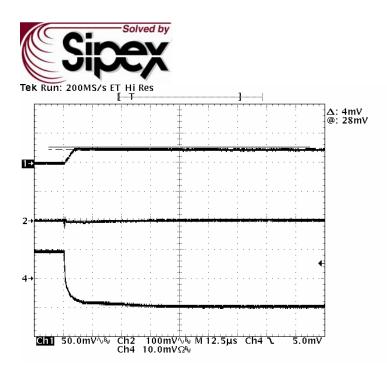


## Test 2

Output Capacitance: 4 x 47uF (188uF total) Transient Description: Sink to Source Output Voltage Overshoot: 10mV

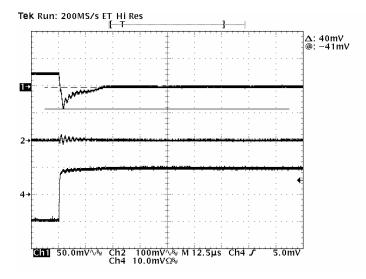


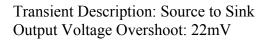
Transient Description: Source to Sink Output Voltage Overshoot = 4mV

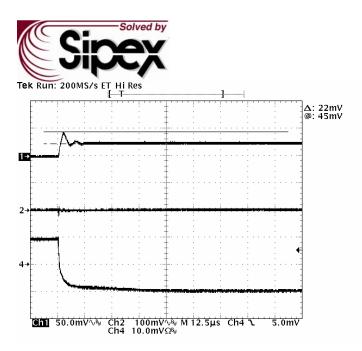


## Test 3

Output Capacitance: 2 x 47uF (96uF total) Transient Description: Sink to Source Output Voltage Overshoot: 40mV







# **Mouser Electronics**

Authorized Distributor

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MaxLinear: SP2996BEN-L/TR SP2996BEN-L